

Shihyun Ahn

List of Publications by Year in descending order

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15
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840776

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15
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citing authors

#	ARTICLE	IF	CITATIONS
1	High Breakdown Voltage (~ 201) β -Ga ₂ O ₃ Schottky Rectifiers. IEEE Electron Device Letters, 2017, 38, 906-909.	3.9	159
2	High reverse breakdown voltage Schottky rectifiers without edge termination on Ga ₂ O ₃ . Applied Physics Letters, 2017, 110, .	3.3	149
3	Effect of front and back gates on β -Ga ₂ O ₃ nano-belt field-effect transistors. Applied Physics Letters, 2016, 109, .	3.3	93
4	Temperature-Dependent Characteristics of Ni/Au and Pt/Au Schottky Diodes on β -Ga ₂ O ₃ . ECS Journal of Solid State Science and Technology, 2017, 6, P68-P72.	1.8	76
5	Inductively coupled plasma etch damage in (-201) Ga ₂ O ₃ Schottky diodes. Applied Physics Letters, 2017, 110, .	3.3	49
6	Inductively coupled plasma etching of bulk, single-crystal Ga ₂ O ₃ . Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2017, 35, .	1.2	32
7	Low dose ⁶⁰ Co gamma-irradiation effects on electronic carrier transport and DC characteristics of AlGa _x N/GaN high-electron-mobility transistors. Radiation Effects and Defects in Solids, 2017, 172, 250-256.	1.2	26
8	Thermal Stability of Implanted or Plasma Exposed Deuterium in Single Crystal Ga ₂ O ₃ . ECS Journal of Solid State Science and Technology, 2017, 6, Q3026-Q3029.	1.8	19
9	Deuterium incorporation and diffusivity in plasma-exposed bulk Ga ₂ O ₃ . Applied Physics Letters, 2016, 109, .	3.3	16
10	Extraction of Migration Energies and Role of Implant Damage on Thermal Stability of Deuterium in Ga ₂ O ₃ . ECS Journal of Solid State Science and Technology, 2017, 6, P794-P797.	1.8	16
11	Characteristics of gate leakage current and breakdown voltage of AlGa _x N/GaN high electron mobility transistors after postprocess annealing. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2014, 32, .	1.2	15
12	Effects of proton irradiation and thermal annealing on off-state step-stressed AlGa _x N/GaN high electron mobility transistors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, .	1.2	11
13	Recovery in dc and rf performance of off-state step-stressed AlGa _x N/GaN high electron mobility transistors with thermal annealing. Applied Physics Letters, 2015, 106, .	3.3	4
14	Evaluation of AlGa _x N/GaN high electron mobility transistors grown on ZrTi buffer layers with sapphire substrates. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, 051208.	1.2	4
15	AlGa _x N/GaN High Electron Mobility Transistor Grown and Fabricated on ZrTi Metallic Alloy Buffer Layers. ECS Journal of Solid State Science and Technology, 2017, 6, S3078-S3080.	1.8	2